GeneSiC™ SEMICONDUCTOR

Silicon Standard Recovery Diode

V_{RRM} = 600 V - 1600 V

I_F = 200 A

Features
• High Surge Capability
• Types up to 1600 V V_{RRM}

Three Tower Package

Maximum ratings, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	MSRT200120(A)	MSRT200140(A)	MSRT200160(A)	Unit
Repetitive peak reverse voltage	V_{RRM}		1200	1400	1600	V
RMS reverse voltage	V_{RMS}		848	990	1131	V
DC blocking voltage	V_{DC}					V
Continuous forward current	I_F	T_C ≤ 140 °C				A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	T_C = 25 °C, t_p = 8.3 ms				A
Operating temperature	T_j					°C
Storage temperature	T_{stg}					°C

Electrical characteristics, at Tj = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Unit
Diode forward voltage	V_F	I_F = 200 A, T_j = 25 °C		V
Reverse current	I_R	V_R = 600 V, T_j = 25 °C		µA
				mA

Thermal characteristics

Parameter	Symbol	Conditions		Unit
Thermal resistance, junction - case	R_{thJC}	0.		°C/W